

- 2 -

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:
Please rewrite claim 1 and add new claim 28 as follows.

Listing of Claims:

Claim 1 (currently amended): A process for producing an oxide single crystal, said process comprising the steps of:

melting a raw material of said oxide single crystal in a crucible;

contacting a seed crystal to a melt of the raw material;

drawing said melt from an opening of said crucible by pulling down the seed crystal;

providing a first heater around said opening of said crucible;

growing the oxide single crystal; and

providing a cooling mechanism for directly cooling said oxide single crystal while said oxide single crystal is being drawn from said opening of said crucible; and

providing a second heater around said oxide single crystal downstream from said cooling mechanism, wherein said cooling mechanism and said second heater are substantially co-linear with respect to one another along the direction in which said oxide single crystal is drawn.

Claim 2 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is cooled by removing ambient heat therefrom.

Claim 3 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is cooled by blowing a cooling medium thereon.

Claim 4 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is drawn from an opening of a nozzle portion provided at a tip of said crucible.

- 3 -

Claim 5 (original): A process for producing an oxide single crystal according to claim 3, wherein said oxide single crystal is drawn from an opening of a nozzle portion provided at a tip of said crucible.

Claim 6 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is of a planar form.

Claim 7 (original): A process for producing an oxide single crystal according to claim 3, wherein said oxide single crystal is of a planar form.

Claim 8 (original): A process for producing an oxide single crystal according to claim 4, wherein said oxide single crystal is of a planar form.

Claim 9 (original): A process for producing an oxide single crystal according to claim 5, wherein said oxide single crystal is of a planar form.

Claim 10-26 (canceled).

Claim 27 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said cooling mechanism directly cools only said oxide single crystal while said oxide single crystal is being drawn from said opening of said crucible.

Claim 28 (new): A process for producing an oxide single crystal according to claim 1, wherein said second heater directly heats said oxide single crystal.